



**Discrete POWER & Signal
Technologies**

1N4150 / FDLL4150



DO-35



LL-34

THE PLACEMENT OF THE EXPANSION GAP
HAS NO RELATIONSHIP TO THE LOCATION
OF THE CATHODE TERMINAL

COLOR BAND MARKING

DEVICE	1ST BAND	2ND BAND
FDLL4150	BLACK	ORANGE

High Conductance Ultra Fast Diode

Sourced from Process 1R.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
W_{IV}	Working Inverse Voltage	50	V
I_O	Average Rectified Current	200	mA
I_F	DC Forward Current	400	mA
I_{fr}	Recurrent Peak Forward Current	600	mA
$I_{f(surge)}$	Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond	1.0 4.0	A A
T_{stg}	Storage Temperature Range	-65 to +200	°C
T_J	Operating Junction Temperature	175	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 200 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		1N / FDLL 4150	
P_D	Total Device Dissipation Derate above 25°C	500 3.33	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	°C/W

High Conductance Ultra Fast Diode

(continued)

1N4150 / FDL4150

Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
B _V	Breakdown Voltage	I _R = 5.0 μA	75		V
I _R	Reverse Current	V _R = 50 V V _R = 50 V, T _A = 150°C		100 100	nA μA
V _F	Forward Voltage	I _F = 1.0 mA I _F = 10 mA I _F = 50 mA I _F = 100 mA I _F = 200 mA	540 660 760 820 0.87	620 740 860 920 1.0	mV mV mV mV V
C _O	Diode Capacitance	V _R = 0, f = 1.0 MHz		2.5	pF
T _{RR}	Reverse Recovery Time	I _F = I _R = 10 mA-200 mA, R _L = 100Ω I _F = I _R = 200 mA-400 mA, R _L = 100Ω		4.0 6.0	nS nS
T _{FR}	Forward Recovery Time	I _F = 200 mA, V _{FR} = 1.0 V		10	nS